1990 GaAs REL WORKSHOP PROGRAM
OCTOBER 7,1990 SHERATON NEW ORLEANS HOTEL, NEW ORLEANS, LOUISIANA

SESSION I HEMT RELIABILITY Kenneth J. Russell , Session Chairman

RECENT LIFE TEST RESULTS ON GaAs HEMTS;
R.H. Maurer, K. Chao, and E. Nhan - Johns Hopkins University Applied Physics Laboratory, Laurel, MD.

ARE HEMT DEVICES READY FOR SPACE APPLICATIONS?;
T. Sacco and S. Kayall - JET Propulsion Laboratory, California Institute of Technology - Pasadena, CA

RELIABILITY OF LOW NOISE AlGaAs/GaAs CONVENTIONAL HEMTS;
W.W. Hu, S.C. Wang, and T.H. Yu - Electronics Laboratory, General Electric Company, Syracuse, NY

RECENT HEMT RELIABILITY RESULTS;
J. Archer, N.G. Bechtel, H. Cooke, and Y.C. Pao - Varian Associates, Inc., Santa Clara, CA

SESSION II ACCELERATED TESTING Edward B. Hakim, Session Chairman

LIFETIME AND FAILURE MECHANISMS OF A 2-6 GHz MMIC AMPLIFIER;
J. Chickanosky, E. Hilston, G. Norris, W. Coughlin, and C. Barratt - Lockheed Sanders, Nashua, NH

PROPOSED JEDEC GUIDELINES FOR FET AND MMIC LIFE TESTS;
B.W. Marks - Texas Instruments, Dallas, TX

FINDING LOW ACTIVATION EVERGY FAILURE MECHANISMS;
W.J. Roesch - TriQuint Semiconductor, Inc., Beaverton, OR

SESSION III ACCELERATED TESTING DISCUSSIONS William J. Roesch, Discussion Moderator

SESSION IV IC RELIABILITY & FAILURE MECHANISMS Walter A. Koziarz, Session Chairman

TEST AND EVALUATION OF DIGITAL GaAs PROCESS CONTROL MONITOR (PCM);
K. Chao and W.C, Wychulls - Applied Physics Laboratory, Johns Hopkins University, Laurel, MD.

GaAs FET MMIC SWITCH RELIABILITY REVISITED;
P. Ersland - M/A-COM Semiconductor Division, Lowell, MA

CONTRIBUTION OF SURFACE AND INTERFACE STATES TO THE REVERSE BIAS AGING OF GaAs SCHOTTKY BARRIERS; K.A. Christianson - University of Maine, Orono, ME

DC CHARACTERIZATION OF ELECTRON AND GAMMA IRRADIATED SARGIC HFETS;
M. Spector, S.B. Witmer, and A. Kanofsky - AT&T, Bell Labs, Reading, PA